



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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## Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

## Features

- $BV_{CEO} > 40V$
- $I_C = 600mA$  High Collector Current
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package

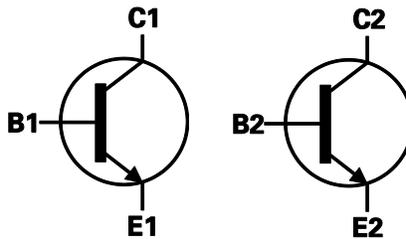
## Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Finish; Solderable per MIL-STD-202, Method 208③
- Weight: 0.006 grams (Approximate)

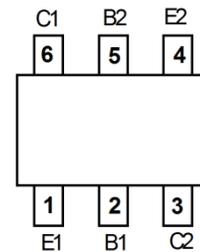


SOT363

Top View



Device Symbol



Top View  
Pin-Out

### Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	$I_C$	600	mA

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_D$	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Operating and Storage and Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

### ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

### Thermal Characteristic and Derating Information

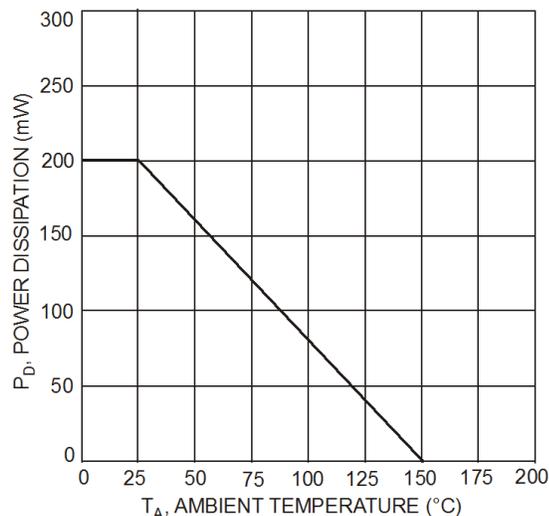


Fig. 1 Max Power Dissipation vs. Ambient Temperature

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	—	V	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 8)	BV <sub>CEO</sub>	40	—	V	I <sub>C</sub> = 10.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	—	V	I <sub>E</sub> = 100μA, I <sub>C</sub> = 0
Collector-Emitter Cut-Off Current	I <sub>CEX</sub>	—	100	nA	V <sub>CE</sub> = 35V, V <sub>EB(OFF)</sub> = 0.4V
Base Cut-Off Current	I <sub>BL</sub>	—	100	nA	V <sub>CE</sub> = 35V, V <sub>EB(OFF)</sub> = 0.4V
<b>ON CHARACTERISTICS (Note 8)</b>					
DC Current Gain	h <sub>FE</sub>	20	—	—	I <sub>C</sub> = 100μA, V <sub>CE</sub> = 1.0V
		40	—		I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 1.0V
		80	—		I <sub>C</sub> = 10mA, V <sub>CE</sub> = 1.0V
		100	300		I <sub>C</sub> = 150mA, V <sub>CE</sub> = 1.0V
		40	—		I <sub>C</sub> = 500mA, V <sub>CE</sub> = 2.0V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	0.40 0.75	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.75	0.95 1.2	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>obo</sub>	—	6.5	pF	V <sub>CB</sub> = 5.0V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>	—	30	pF	V <sub>EB</sub> = 0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Input Impedance	h <sub>ie</sub>	1.0	15	kΩ	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h <sub>re</sub>	0.1	8.0	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>fe</sub>	40	500	—	
Output Admittance	h <sub>oe</sub>	1.0	30	μs	
Current Gain-Bandwidth Product	f <sub>T</sub>	250	—	MHz	V <sub>CE</sub> = 30V, I <sub>C</sub> = 150mA, f = 100MHz
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	t <sub>D</sub>	—	15	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA, V <sub>BE(OFF)</sub> = 2.0V, I <sub>B1</sub> = 15mA
Rise Time	t <sub>R</sub>	—	20	ns	
Storage Time	t <sub>S</sub>	—	225	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA, I <sub>B1</sub> = - I <sub>B2</sub> = 15mA
Fall Time	t <sub>F</sub>	—	30	ns	

Note: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

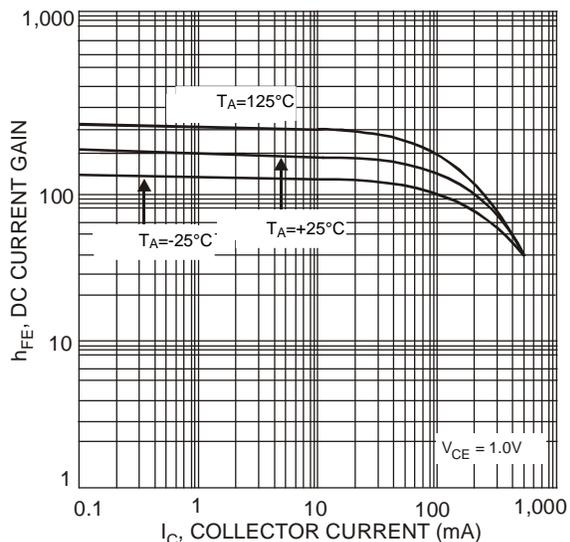


Fig. 2 Typical DC Current Gain vs. Collector Current

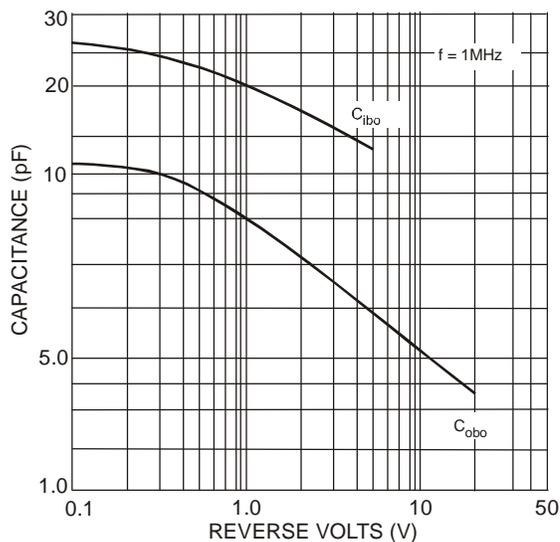


Fig. 3 Typical Capacitance

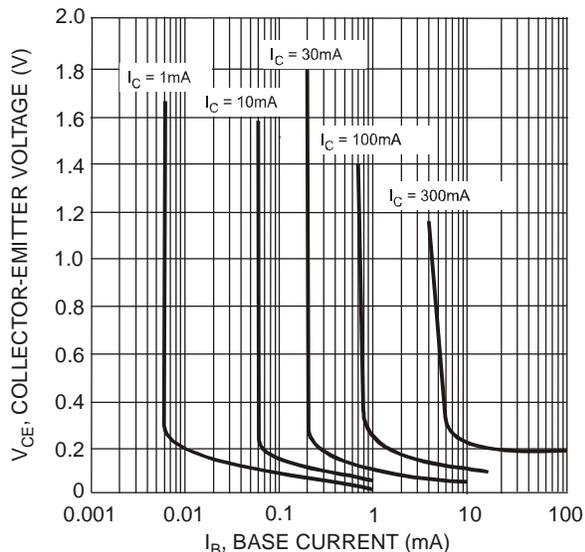


Fig. 4 Typical Collector Saturation Region

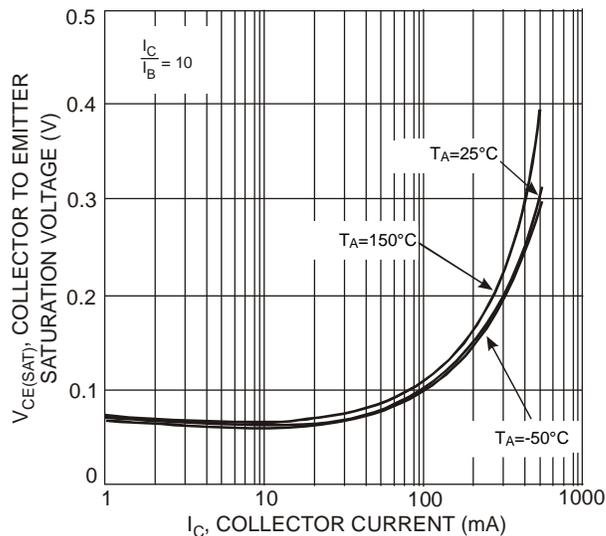


Fig. 5 Collector Emitter Saturation Voltage vs. Collector Current

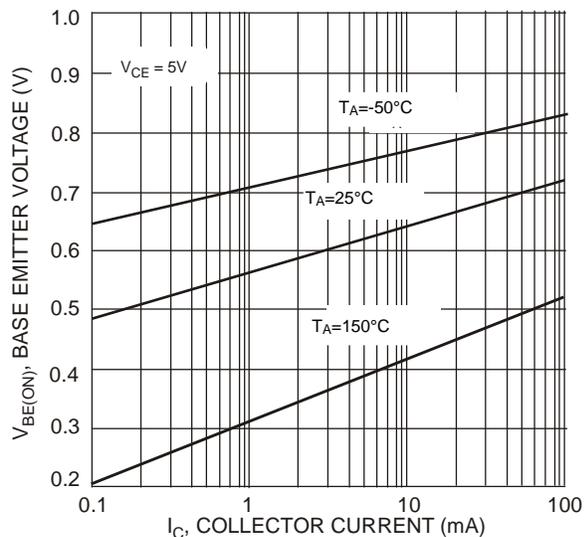


Fig. 6 Base Emitter Voltage vs. Collector Current

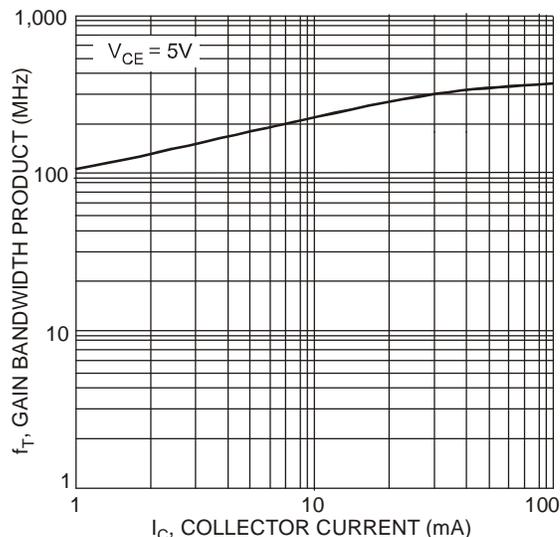
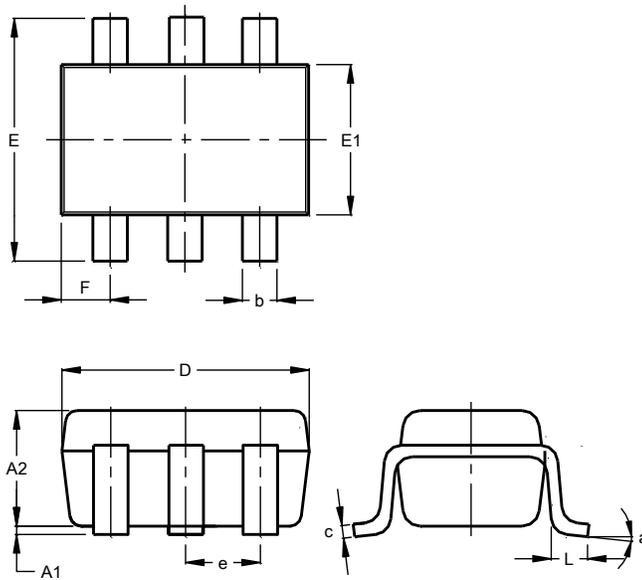


Fig. 7 Gain Bandwidth Product vs. Collector Current

## Package Outline Dimensions

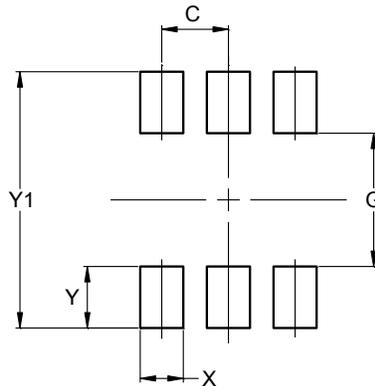
SOT363



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500